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=> FIL REG
FILE 'REGISTRY' ENTERED AT 14:23:50 ON 01 APR 2009
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     FILE 'LCA' ENTERED AT 13:18:18 ON 01 APR 2009
L1          364 SEA (VALVE? OR METAL#### OR NIOBIUM? OR ALOY? OR
                AMALGAM? OR INGOT? OR BULLION?) (2A) (PENTOXIDE? OR
                OXIDE? OR DIOXIDE? OR SUBOXIDE? OR SUB (2A) OXIDE)
L2            2 SEA GETTER? (2A) (MATERIAL? OR GAS### OR SUBSTANCE?)
L3         2173 SEA HYDROGEN OR 1333-74-0 OR H2 OR NOBLE (2A) GAS
L4         5586 SEA PARTICL? OR MICROPARTICL? OR PARTICULAT? OR DUST? OR
                GRIT? OR GRAIN# OR GRANUL? OR POWDER? OR SOOT? OR SMUT?
                OR FINES# OR PRILL? OR FLAKE# OR PELLET? OR BB#
L5           13 SEA (OXYGEN? OR O2) (2A) REDUC?
L6            0 SEA B213 OR B (A) 213
L7           79 SEA ASTM#
L8          182 SEA CAPACIT!R? OR CAPACITANC? OR CAPACIT!R (2A) ELECTRODE
                ?
L9           31 SEA (FLOW OR FLOWS OR FLOWED OR FLOWING#) (2A) (VALUE?
                OR PARAMETER? OR NUMBER? OR NUMBERICAL? OR THRESHOLD? OR
                LIMIT?)
L10          21 SEA (MILLIG? OR MG#) (W) (S OR SECOND# OR SEC#)
L11         153 SEA (FLOW OR FLOWS OR FLOWED OR FLOWING#) (2A) (HIGH? OR
                INCREAS? OR ELEVAT? OR HEIGHTEN? OR RAIS? OR AUGMENT? OR
                LARGE? OR GREAT?)

     FILE 'LREGISTRY' ENTERED AT 13:36:59 ON 01 APR 2009
L12           5 SEA (NB (L) O)/ELS (L) 2/ELC.SUB

     FILE 'REGISTRY' ENTERED AT 13:38:21 ON 01 APR 2009
L13         279 SEA (NB (L) O)/ELS (L) 2/ELC.SUB
                E NIOBIUM/CN
L14           1 SEA NIOBIUM/CN
     FILE 'LCA' ENTERED AT 13:43:17 ON 01 APR 2009
L15           8 SEA GETTERS/IT
L16          19 SEA GRANULATION/IT

     FILE 'LREGISTRY' ENTERED AT 13:45:37 ON 01 APR 2009
L17           2 SEA (NB (L) H)/ELS (L) 2/ELC.SUB

     FILE 'REGISTRY' ENTERED AT 13:46:49 ON 01 APR 2009
L18         159 SEA (NB (L) H)/ELS (L) 2/ELC.SUB
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     FILE 'STNGUIDE' ENTERED AT 13:47:35 ON 01 APR 2009
L19           0 SEA GETTER?

     FILE 'REGISTRY' ENTERED AT 13:51:07 ON 01 APR 2009
                 E NIOBIUM OXIDE/CN
L20           2 SEA "NIOBIUM OXIDE"/CN

     FILE 'HCA' ENTERED AT 13:52:44 ON 01 APR 2009
L21       20098 SEA L13 OR L20
L22       73115 SEA L14
L23         681 SEA L18
L24          21 SEA L19 AND L21
L25          14 SEA L24 AND (VALV? OR L22 OR L23 OR L8 OR L4 OR L5 OR
                 L3)

     FILE 'REGISTRY' ENTERED AT 14:01:57 ON 01 APR 2009
                 E HYDROGEN/CN
L26           1 SEA HYDROGEN/CN

     FILE 'HCA' ENTERED AT 14:02:13 ON 01 APR 2009
L27      356645 SEA L26
L28           7 SEA L24 AND L27

     FILE 'HCA' ENTERED AT 14:04:05 ON 01 APR 2009
L29         180 SEA L19 AND VALV?
L30           2 SEA L29 AND L21
L31          11 SEA L29 AND L22
L32           1 SEA L29 AND L23
L33          23 SEA L25 OR L28 OR L30 OR L32 OR L31
L34           7 SEA L24 NOT L33
L35         349 SEA L8 AND (L9 OR L10 OR L11)
L36          74 SEA L8 AND L9
L37          13 SEA L8 AND L10
L38         269 SEA L8 AND L11
L39           7 SEA L36 AND L38
L40           0 SEA L8 AND L6
L41          63 SEA L8 AND L7
L42           0 SEA L41 AND (L9 OR L10 OR L11)
L43           0 SEA L6 AND (L9 OR L10 OR L11)
L44         203 SEA B213 OR B (A) 213
L45           1 SEA L44 AND L7
     FILE 'HCA' ENTERED AT 14:18:20 ON 01 APR 2009
L46           0 SEA L41 AND L36
L47           0 SEA L41 AND L38
L48           0 SEA L21 AND L36
L49           2 SEA L21 AND L38
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L50 0 SEA L21 AND L41
L51 23 SEA L37 OR L39 OR L45 OR L49
L52 20 SEA 1808-2003/PY,PRY,AY AND L33
L53 6 SEA 1808-2003/PY,PRY,AY AND L34
L54 18 SEA 1808-2003/PY,PRY,AY AND L51

=> FIL HCA

FILE 'HCA' ENTERED AT 14:24:00 ON 01 APR 2009

(SEARCH OF REQUEST'S "ADDITIONAL COMMENTS")

=> D L54 1-18 BIB ABS HITRN HITIND RE

L54 ANSWER 1 OF 18 HCA COPYRIGHT 2009 ACS on STN
AN 136:13484 HCA Full-text
TI SiO2 films deposited on silicon at low temperature by plasma-enhanced decomposition of hexamethyldisilazane: Defect characterization
AU Croci, S.; Pecheur, A.; Autran, J. L.; Vedda, A.; Caccavale, F.; Martini, M.; Spinolo, G.
CS Laboratoire de Physique de la Matiere, UMR CNRS 5511, Institut National des Sciences Appliquees de Lyon, Villeurbanne, F-69621, Fr.
SO Journal of Vacuum Science & Technology, A: Vacuum, Surfaces, and Films (2001), 19(5), 2670-2675
CODEN: JVTAD6; ISSN: 0734-2101
PB American Institute of Physics
DT Journal
LA English
AB Silicon dioxide films have been deposited by plasma-enhanced chem. vapor deposition at low substrate temp. (50°C) in a parallel-plate reactor using hexamethyldisilazane (HMDS), dild. in He, and O2 as Si and O precursors. The effect of the O2/(HMDS+He) flow rate ratio on the oxide properties has been investigated in the range of 0.05-1.25 by means of deposition rate, wet etching rate, secondary ion mass spectrometry, thermally stimulated luminescence, and high frequency capacitance-voltage measurements. Both the deposition rate and the etching rate increase by increasing the O2/(HMDS+He) flow rate ratio and reach a const. value at flow rate ratios higher than 0.6. The strong increase and satn. in the deposition rate can be attributed to